

PD1900-35T52 InAsP PIN-PD

PD1900-35T52 is InAsP stepped layers type InAsP PIN-photodiode can be used at room temperature.

This PIN-photodiode is consists of a large chip with 0.35x0.35mm active area mounted on the TO-18 stem and is hermetical sealed by metal can with flat lens.

These devices are designed to be easy of setting up optically with a wide angle of half sensitivity of $\pm 40^\circ$.

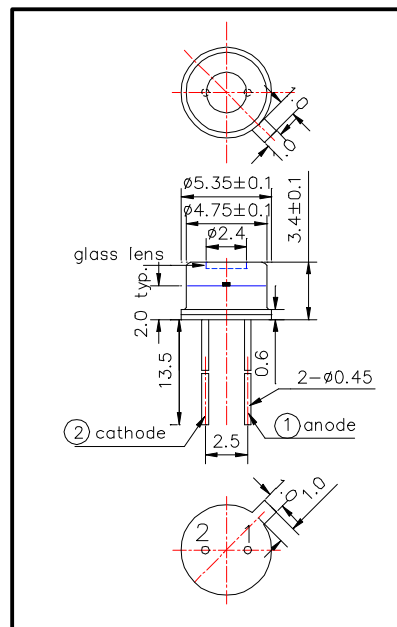
Features

- 1) Operative at Room Temperature
- 2) High Reliability
- 3) High Response

Specifications

- 1) Product Name InAsP PIN Photo-Diode
- 2) Type No. PD1900-35T52
- 3) Chip
 - (1) Active Area 0.35mmx0.35mm
- 4) Package
 - (1) Type TO-18
 - (2) Lens Glass Flat Lens (f2.4)
 - (3) Cap Gold Plated

Outer dimension(Unit:mm)



Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	2	V
Operating Temperature	T_{OPR}	-20 ~ +90	°C
Storage Temperature	T_{STG}	-30 ~ +100	°C
Soldering Temperature	T_{SOL}	240	°C

‡ Pulse Soldering condition: Soldering condition must be completed within 2 seconds at 240°C

Electro-Optical Characteristics [25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	unit
Photo Responsivity	R_E	$V_R=0V, I_P=1950nm$		1.2		A/W
Photo Current	I_L	$V_R=0V, I_P=1950nm$		16		uA(± 1)
Dark Current	I_D	$V_R=1V$			5000	nA
Spectral Responsivity (Peak)	I_P	$V_R=0V$	1300		2100	nm
Half Angle of Sensitivity	$Q_{1/2}$	$V_R=0V$		±40		deg.
Total Capacitance	C_T	$f=1MHz, V_R=1V$		20		pF
Rise/Fall Time(10%~90%)	t_r	$R_L=1K, V_R=1V$		5		ns
	t_f			5		ns

‡ Measured by Epitex' s calibrated tool